

**UV – Photodiode with
integrated amplifier****JIC 149 E**

- characteristics :**
- ◆ SiC-photodiode with integrated special filter
 - ◆ response approximately (CIE 87)
 - ◆ optimized for solar application
 - ◆ active area 0,22 mm²
 - ◆ extra sensor pin for external adjustment of gain and bandwidth
 - ◆ single supply voltage
 - ◆ sensor assembly isolated to ground
 - ◆ full hermetically sealed package
 - ◆ components are in conformity with RoHS and WEEE

- applications :**
- ◆ UV-measurement only
 - ◆ measurement of erythema efficient UV-part on natural sunlight

absolute maximum ratings :

reverse voltage	20 V
operating temperature range	- 25 °C ... 70 °C
storage temperature range	-40 °C ... 100 °C
welding temperature (3s)	260 °C

technical data :

common test conditions if not otherwise specified: $T_A = 25\text{ °C}$, $V_R = 0\text{ V}$
(typical values in brackets)

parameter	test condition	JIC 149E	unit
transimpedance		1.000	MΩ
dark offset voltage	$E = 0\text{ lx}$	± 3	mV
noise voltage	$B = 1\text{ kHz}$	1	mV _{rms}
max. spectral response	$\lambda = 295\text{ nm}$	100	mV/nW
risetime		600	μs
bandwidth	- 3 dB	0,5	kHz
saturation voltage	$R_L = 2\text{ k}\Omega$	+ 4,95 (+ 4,8)	V
short current		± 50	mA
supply voltage		+ 2,7...+ 5	V
current consumption		750 (1100)	μA

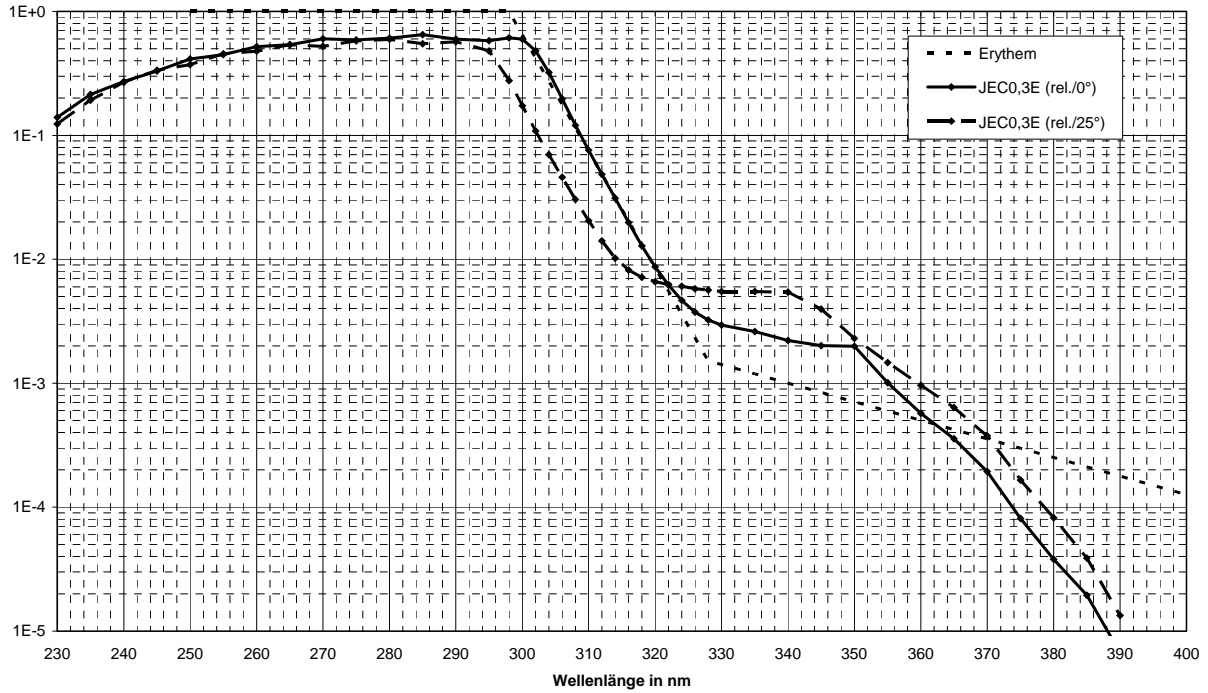
rev. 2 (03/2009)

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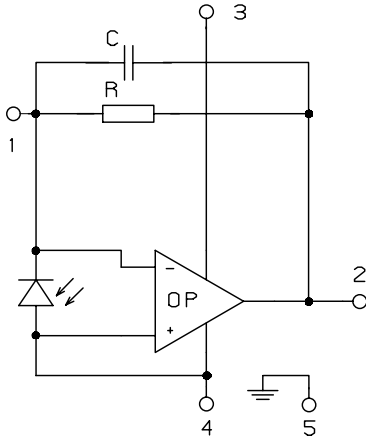
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relative spectral response

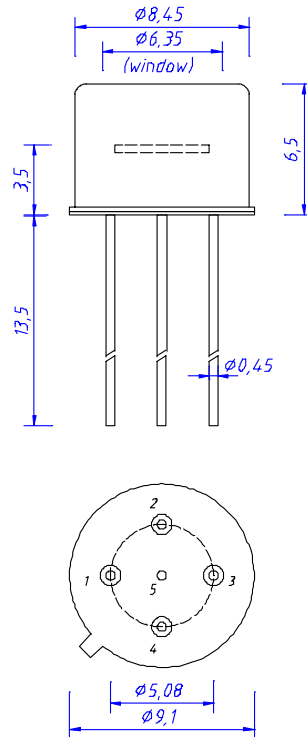


internal circuit



- 1 R_f
- 2 Out
- 3 V_s
- 4 GND
- 5 Case

package dimension



applicartion hints:

- If an external resistor for reduction of gain is used, please make sure that lenght of connectors is as short as possible to reduce noise and capacitive interference.
- If internally adjusted gain is used only, please cut pin „1“.